

Notice of References Cited		Application/Control No. 10/749,771	Applicant(s)/Patent Under Reexamination SHYU ET AL.	
		Examiner Evan Pert	Art Unit 2826	Page 1 of 1

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	C	US-5,142,438 A	08-1992	Reinberg et al.	361/313
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NON-PATENT DOCUMENTS

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	U	Senzaki et al., "Atomic Layer Deposition of High-k Thin Films for Gate and Capacitor Dielectrics," 2004 International Conference on Integrated Circuit Design and Technology, pages 269-274.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.